In the Specification

Please amend paragraph [0022] as follows:

[0022] A dopant 66 is implanted at an angle into substrate 12 to form pocket implant regions 68 and 70 relative to the transistor devices 52 and 54, respectively. Implant 66 is referred to as an "angled" implant, to emphasize that the implant is at an angle other than 0° relative to a vertical direction. In the diagram of Fig. 5, an axis 68 is provided to illustrate a vertical direction (such direction is substantially orthogonal to a substantially planar upper surface of substrate 12), and an angle θ is provided to ~~shown~~ show the relative angle of implant 66 to the vertical direction. Angle θ has an absolute magnitude greater than 0°.

Please amend paragraph [0024] as follows:

[0024] An additional implant which can be performed at the processing stage of Fig. 5 is a lightly doped diffusion (LDD) implant. The LDD implant is typically straight into substrate 12 (i.e., implanted with angle θ of 0 degrees), and forms a region overlapping region 48. The dopant of the LDD implant can subsequently be diffused to extend outwardly beyond region 48. The LDD implant is not shown in Fig. 5. The LDD region would typically be formed to have a dopant concentration of from about 10^{19} atoms/cm^3 to about 5×10^{20} atoms/cm^3.